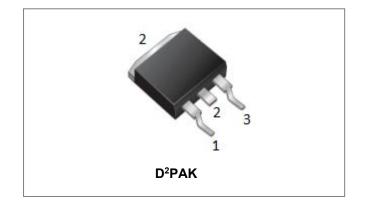


18TQ035S 18TQ045S

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18TQ035S 18TQ045S SCHOTTKY RECTIFIER



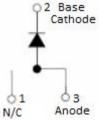
Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- **Terminals finish: 100% Pure Tin**
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters •
- **Free-Wheeling diodes**
- **Reverse battery protection**
- Center tap configuration

Circuit Diagram



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	18TQ035S(35) 18TQ045S(45)	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=105°C, rectangular wave form	18	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	390	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.41	0.50	V
	V _{F2}	@ 18A, Pulse, T _J = 25 °C	0.50	0.60	V
Reverse Current at DC condition*	I _{R1}	$@V_R = rated V_{R_{,,}} T_J = 25 \ ^{\circ}C$	0.08	2.5	mA
	I _{R2}	$@V_R = rated V_{R,} T_J = 125 \circ C$	15	30	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	680	1400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

* Pulse width < 300 µs, duty cycle < 2%

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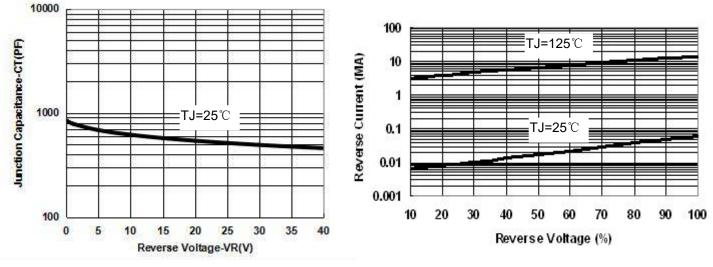


RoHS 🗭

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units		
Junction Temperature	TJ	-	-55 to +150	°C		
Storage Temperature	T _{stg}	-	-55 to +150	°C		
Typical Thermal Resistance Junction to Case	Rejc	DC operation	6	°C/W		
Approximate Weight	wt	-	1.85	g		
Case Style	D ² PAK					





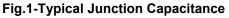


Fig.2-Typical Reverse Characteristics

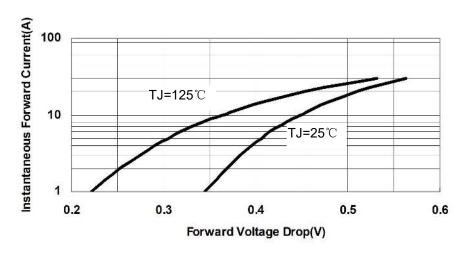
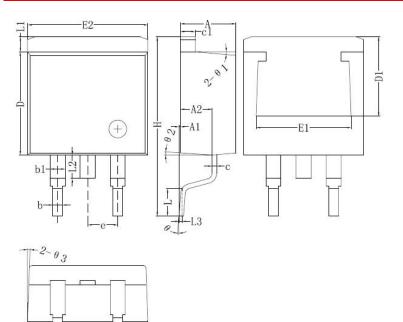


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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Mechanical Dimensions D²PAK



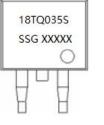
Symbol	Dimensions in millimeters				
	Min.	Typical	Max.		
Α	4.47	4.70	4.85		
A1	0	0.10	0.25		
A2	2.59	2.69	2.89		
b	0.71	0.81	0.96		
b1	1.17	1.27	1.37		
С	0.31	0.38	0.61		
c1	1.17	1.27	1.37		
D	8.50	8.70	8.90		
D1	6.40				
E	10.01	10.16	10.31		
E1	7.6				
E2	9.98	10.08	10.31		
е		2.54			
Н	14.6	15.1	15.6		
L	2.00	2.30	2.74		
L1	1.12	1.27	1.42		
L2	1.30		2.20		
L3		0.25BSC			
е	0	-	8°		
e1		5°			
e2		4°			
e3		4°			

Ordering Information

Device	Package	Shipping
18TQ035S 18TQ045S	D ² PAK	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

18

TQ 35/45

S

SSG

ΥY

WW

L

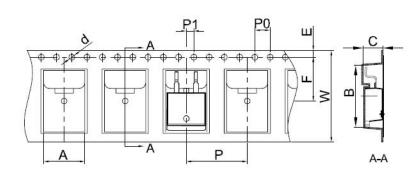
- = Forward Current (18A)
- = Device Type = Reverse Voltage(45V)
- = Package type
- = SSG

= Year

= Week = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK



OVMDOL	Millimeters				
SYMBOL	Min.	Max.			
A	10.70	10.90			
В	16.03	16.23			
С	5.11	5.31			
d	1.45	1.65			
E	1.65	1.85			
F	11.40	11.60			
P0	3.90	4.10			
Р	15.90	16.10			
P1	1.90	2.10			
W	23.90	24.30			

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